

20V Dual P-Channel MOSFET



TSSOP-8

Pin Definition:

1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2

5. Gate 2

PRODUCT SUMMARY

| V _{DS} (V) | $R_{DS(on)}(m\Omega)$ | I _D (A) | |
|---------------------|------------------------------|--------------------|--|
| -20 | 40 @ V _{GS} = -4.5V | -5 | |
| | 50 @ V _{GS} = -2.5V | -4 | |
| | 60 @ V _{GS} = -1.8V | -3 | |

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

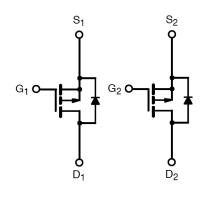
Application

- Load Switch
- PA Switch

Ordering Information

| Part No. | Package | Packing |
|---------------|---------|---------|
| TSM6981DCA RF | TSSOP-8 | T&R |

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|--|-------------------------|-----------------------------------|--------------|------|
| Drain-Source Voltage | | V_{DS} | -20 | V |
| Gate-Source Voltage | | V_{GS} | ±8 | V |
| Continuous Drain Current, V _{GS} @4.5V. | | I _D | -5 | А |
| Pulsed Drain Current, V _{GS} @4.5V | | I _{DM} | -30 | А |
| Continuous Source Current (Diode Cond | luction) ^{a,b} | Is | -1.0 | А |
| Manianum Danuar Discipation | Ta = 25 °C | | 1.14 | \A/ |
| Maximum Power Dissipation | | 0.73 | W | |
| Operating Junction Temperature | | T _J | +150 | °C |
| Operating Junction and Storage Temper | ature Range | T _J , T _{STG} | - 55 to +150 | °C |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|--|------------------|-------|------|
| Junction to Foot (Drain) Thermal Resistance | R⊖ _{JF} | 40 | °C/W |
| Junction to Ambient Thermal Resistance (PCB mounted) | RO _{JA} | 75 | °C/W |

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature



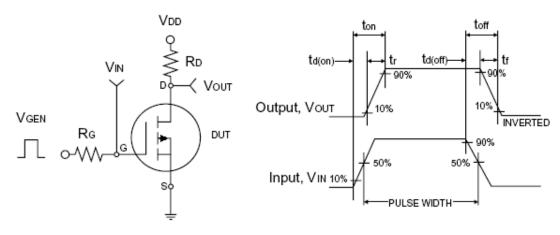
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COMPLIANCE Electrical Specifications

| Parameter | Conditions | Symbol | Min | Тур | Max | Unit |
|----------------------------------|--|---------------------|------|-------|------|------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = -250uA$ | BV _{DSS} | -20 | | | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = -250uA$ | $V_{GS(TH)}$ | -0.4 | | -1.0 | V |
| Zero Gate Voltage Drain Current | $V_{DS} = -16V, V_{GS} = 0V$ | I _{DSS} | | | -1.0 | uA |
| Gate Body Leakage | $V_{GS} = \pm 8V, V_{DS} = 0V$ | I _{GSS} | | | ±100 | nA |
| On-State Drain Current | V _{DS} ≤-5V, V _{GS} = -4.5V | I _{D(ON)} | -20 | | | Α |
| | $V_{GS} = -4.5V, I_D = -5A$ | | | 30 | 30 | |
| Drain-Source On-State Resistance | $V_{GS} = -2.5V, I_D = -4A$ | R _{DS(ON)} | | 40 | 50 | mΩ |
| | $V_{GS} = -1.8V, I_D = -3A$ | | | 50 | 60 | |
| Forward Transconductance | $V_{DS} = -5V, I_{D} = -5A$ | 9 _{fs} | | 17 | | S |
| Diode Forward Voltage | I _S = - 1.0A, V _{GS} = 0V | V_{SD} | | - 0.6 | -1.2 | V |
| Dynamic ^b | | | | | | |
| Total Gate Charge | $V_{DS} = -10V, I_{D} = -4.7A,$ | Q_g | | 12.5 | 19 | |
| Gate-Source Charge | $V_{DS} = -10V, I_D = -4.7A,$ $V_{GS} = -4.5V$ | Q_{gs} | | 1.7 | | nC |
| Gate-Drain Charge | V _{GS} = -4.5V | Q_{gd} | | 3.3 | | |
| Input Capacitance | \/ - 40\/ \/ - 0\/ | C _{iss} | | 1020 | | |
| Output Capacitance | $V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz | C _{oss} | | 191 | | pF |
| Reverse Transfer Capacitance | 7 I = 1.0IVID2 | C _{rss} | | 140 | | |
| Switching ^c | | | | | | |
| Turn-On Delay Time | $V_{DD} = -10V, R_L = 10\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ | t _{d(on)} | | 25 | 40 | |
| Turn-On Rise Time | | t _r | | 43 | 65 | 20 |
| Turn-Off Delay Time | | t _{d(off)} | | 71 | 110 | nS |
| Turn-Off Fall Time | $R_G = 6\Omega$ | t _f | | 48 | 75 | |

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

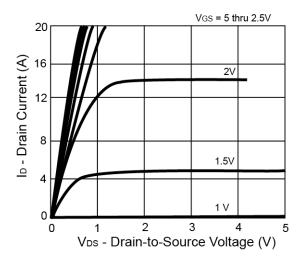


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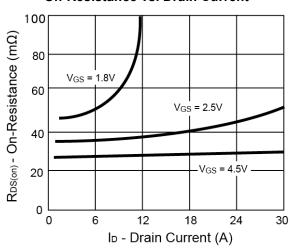


Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

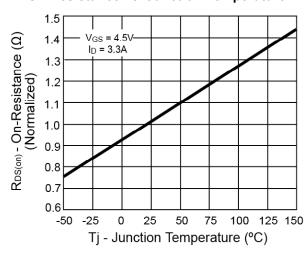
Output Characteristics



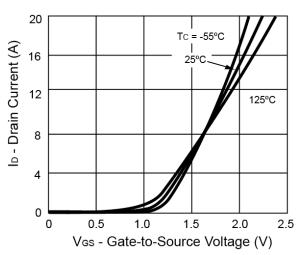
On-Resistance vs. Drain Current



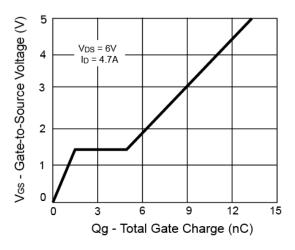
On-Resistance vs. Junction Temperature



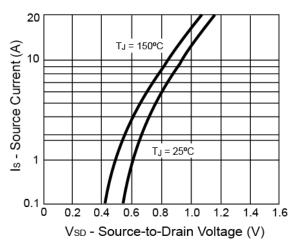
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



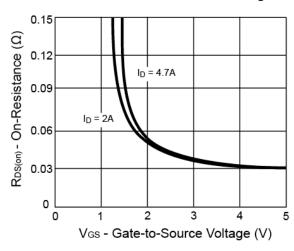


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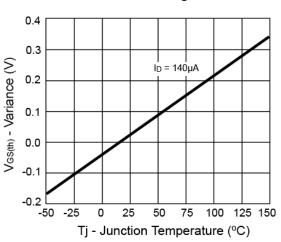


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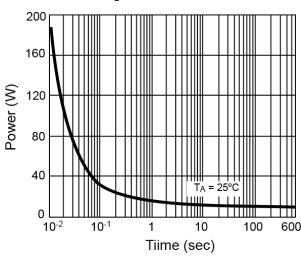
On-Resistance vs. Gate-Source Voltage



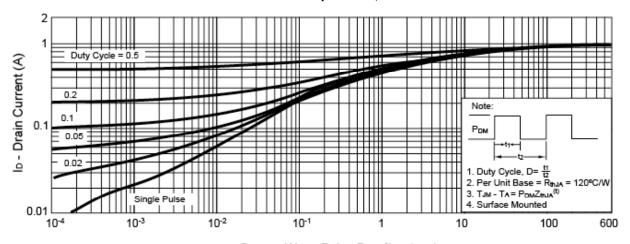
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



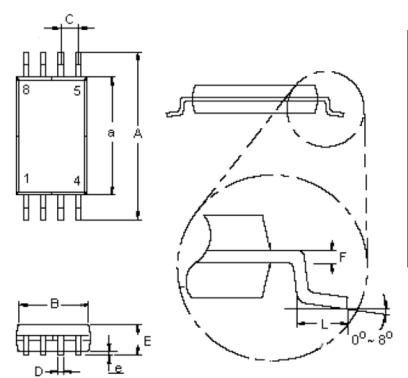
Square Wave Pulse Duration (sec)



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TSSOP-8 Mechanical Drawing



| | TSSOP-8 DIMENSION | | | | |
|-----|-------------------|------|-------------|-------|--|
| DIM | MILLIMETERS | | INCHES | | |
| | MIN | MAX | MIN | MAX | |
| Α | 6.20 | 6.60 | 0.244 | 0.260 | |
| а | 4.30 | 4.50 | 0.170 | 0.177 | |
| В | 2.90 | 3.10 | 0.114 | 0.122 | |
| C | 0.65 (typ) | | 0.025 (typ) | | |
| D | 0.25 | 0.30 | 0.010 | 0.019 | |
| Е | 1.05 | 1.20 | 0.041 | 0.049 | |
| е | 0.05 | 0.15 | 0.002 | 0.009 | |
| F | 0.127 | | 0.005 | | |
| L | 0.50 | 0.70 | 0.020 | 0.028 | |
| | | | | | |



TSM6981D 20V Dual P-Channel MOSFET

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